Analog Power AM1370N

N-Channel 180-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

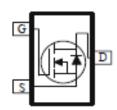
Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)		
180	1500 @ V _{GS} = 10V	0.39		
	1600 @ V _{GS} = 4.5V	0.38		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter			Symbol	Limit	Units		
Drain-Source Voltage				180	V		
Gate-Source Voltage				±20	V		
Continuous Drain Correct®		T _A =25°C	_	0.39			
Continuous Drain Current ^a		T _A =70°C	I _D	0.32	Α		
Pulsed Drain Current ^b	I _{DM}	2					
Continuous Source Current (Diode Conduction) a	I _S	0.45	Α				
Dower Dissipation a		T _A =25°C	P _D	0.34	W		
Power Dissipation ^a			' D	0.22	V V		
Operating Junction and Storage Temperature Range				-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	375	°C/W			
Maximum Junction-to-Ambient	Steady State	IXOJA	430	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 144 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 144 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	1			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_D = 0.3 \text{ A}$			1500	0 mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 0.24 \text{ A}$			1600	11122	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 0.3 \text{ A}$		28		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 0.23 \text{ A}, V_{GS} = 0 \text{ V}$		0.71		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 90 \text{ V}, V_{GS} = 4.5 \text{ V},$		3.0			
Gate-Source Charge	Q_{gs}	$I_{DS} = 90 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 0.3 \text{ A}$		0.8		nC	
Gate-Drain Charge	Q_{gd}	1B = 0.0 A		1.5			
Turn-On Delay Time	t _{d(on)}	V = 00 V B = 300 O		3			
Rise Time	t _r	$V_{DS} = 90 \text{ V}, R_L = 300 \Omega,$ $I_D = 0.3 \text{ A},$		4		no	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		14		ns	
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.12		8			
Input Capacitance	C _{iss}			163			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		12		pF	
Reverse Transfer Capacitance	C_{rss}			11			

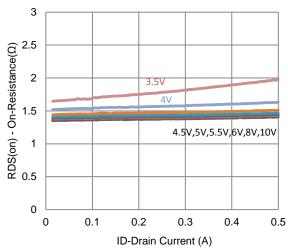
Notes

- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

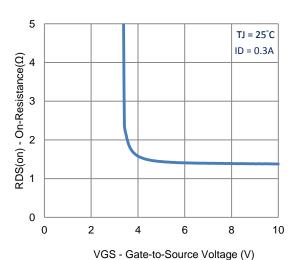
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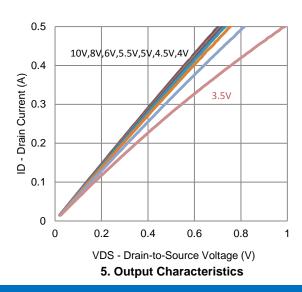
Typical Electrical Characteristics

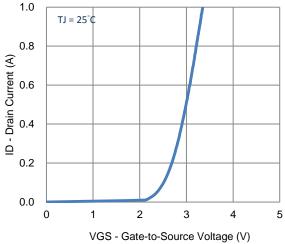


1. On-Resistance vs. Drain Current

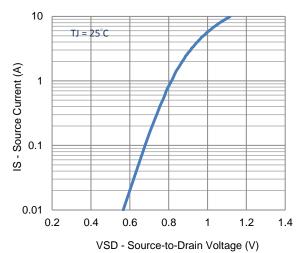


3. On-Resistance vs. Gate-to-Source Voltage

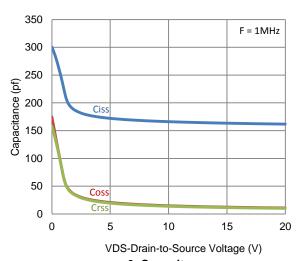




2. Transfer Characteristics



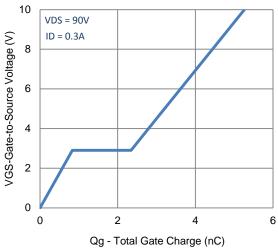
4. Drain-to-Source Forward Voltage



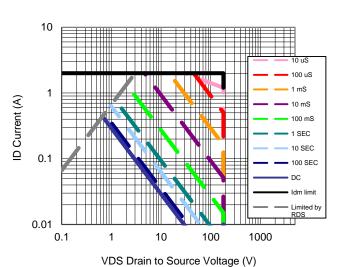
6. Capacitance

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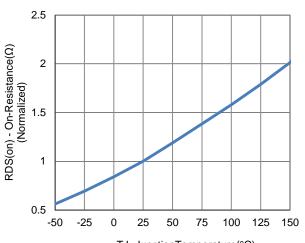
Typical Electrical Characteristics





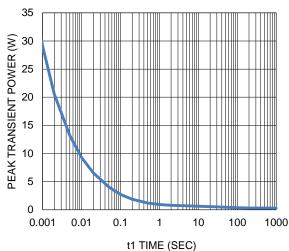


9. Safe Operating Area

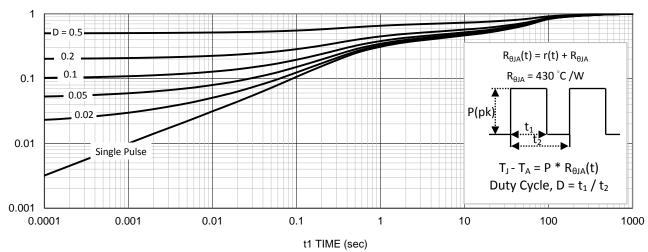


TJ -JunctionTemperature(°C)

8. Normalized On-Resistance Vs **Junction Temperature**



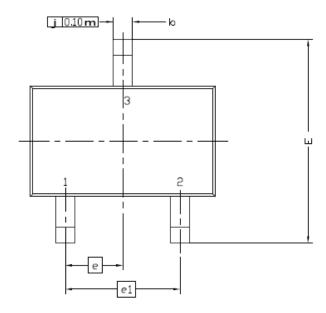
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

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Package Information



DIM.	MILLIMETERS			INCHES			
	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.900	0,95	1.10	0,035	0,037	0.043	
A1	0.00	-	0.10	0.000		0.004	
A2	0.70	0.90	1.00	0.028	0.035	0.039	
lo	0.15	0.22	0.30	0.006	0.016	0.012	
C	0.08	0.127	0.20	0.003	0,005	0.008	
D	2.10 BSC			0.083 BSC			
E	2.30 BSC			0.091 BSC			
E1	1,30 BSC			0.051 BSC			
6	0.65 BSC			0.026 BSC			
e1	1,30 BSC			0.051 BSC			
L	0.26	0.40	0.46	0.010	0,015	0.018	
L2	0.254BSC			0,010BSC			
R	0.10			0.004			
θ	0°	4°	8°	0°	4°	ϡ	
θ1	7°N□M				7°N□M		

